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TABLE OF CONTENTS

1.1 - MULTI-CHIP TECHNOLOGIES TO UNLEASH COMPUTING PERFORMANCE GAINS OVER THE NEXT DECADE.....	1
<i>Lisa T. Su ; Samuel Naffziger ; Mark Papermaster</i>	
1.2 - ENERGY EFFICIENT COMPUTING AND SENSING IN THE ZETTABYTE ERA: FROM SILICON TO THE CLOUD.....	9
<i>Adrian M. Ionescu</i>	
1.3 - SYSTEM SCALING FOR INTELLIGENT UBIQUITOUS COMPUTING.....	17
<i>Jack Y. -C. Sun</i>	
2.1 - BREAKTHROUGH OF SELECTOR TECHNOLOGY FOR CROSS-POINT 25-NM RERAM.....	24
<i>Soo Gil Kim ; Jong Chul Lee ; Tae Jung Ha ; Jong Ho Lee ; Jae Yeon Lee ; Yong Taek Park ; Kyung Wan Kim ; Won Ki Ju ; Young Seok Ko ; Hyun Mi Hwang ; Bo Mi Lee ; Joo Young Moon ; Woo Young Park ; Byung Gu Gyun ; Byoung-Ki Lee ; Donggyu Yim ; Sung-Joo Hong</i>	
2.2 - AN ULTRA HIGH ENDURANCE AND THERMALLY STABLE SELECTOR BASED ON TEASGESISE CHALCOGENIDES COMPATIBLE WITH BEOL IC INTEGRATION FOR CROSS-POINT PCM.....	28
<i>H. Y. Cheng ; W. C. Chien ; I. T. Kuo ; E. K. Lai ; Y. Zhu ; J. L. Jordan-Sweet ; A. Ray ; F. Carta ; F. M. Lee ; P. H. Tseng ; M. H. Lee ; Y. Y. Lin ; W. Kim ; R. Bruce ; C. W. Yeh ; C. H. Yang ; M. Brightsky ; H. L. Lung</i>	
2.3 - IN-DEPTH INVESTIGATION OF PROGRAMMING AND READING OPERATIONS IN RRAM CELLS INTEGRATED WITH OVONIC THRESHOLD SWITCHING (OTS) SELECTORS.....	32
<i>M. Alayan ; E. Vianello ; G. Navarro ; C. Carabasse ; S. La Barbera ; A. Verdy ; N. Castellani ; A. Levisse ; G. Molas ; L. Grenouillet ; T. Magis ; F. Aussenac ; M. Bernard ; B. Desalvo ; J. M. Portal ; E. Nowak</i>	
2.4 - BEOL BASED RRAM WITH ONE EXTRA-MASK FOR LOW COST, HIGHLY RELIABLE EMBEDDED APPLICATION IN 28 NM NODE AND BEYOND.....	36
<i>Hangbing Lv ; Xiaoxin Xu ; Peng Yuan ; Danian Dong ; Tiancheng Gong ; Jing Liu ; Zhaoan Yu ; Peng Huang ; Kun Zhang ; Changxing Huo ; Chanbing Chen ; Yuanlu Xie ; Qing Luo ; Shibing Long ; Qi Liu ; Jinfeng Kang ; Daisy Yang ; Simon Yin ; Shengfen Chiu ; Ming Liu</i>	
2.5 - A COMPREHENSIVE STUDY OF 3-STAGE HIGH RESISTANCE STATE RETENTION BEHAVIOR FOR TMO RERAMS FROM SINGLE CELLS TO A LARGE ARRAY.....	40
<i>Yu-Hsuan Lin ; Yung-Han Ho ; Ming-Hsiu Lee ; Chao-Hung Wang ; Yu-Yu Lin ; Feng-Ming Lee ; Kai-Chieh Hsu ; Po-Hao Tseng ; Dai-Ying Lee ; Kuang-Hao Chiang ; Keh-Chung Wang ; Tseung-Yuen Tseng ; Chih-Yuan Lu</i>	
2.6 - INTEGRATED HFO₂-RRAM TO ACHIEVE HIGHLY RELIABLE, GREENER, FASTER, COST-EFFECTIVE, AND SCALED DEVICES.....	44
<i>Chiahua Ho ; Shuo-Che Chang ; Chao-Yi Huang ; Yu-Cheng Chuang ; Seow-Fong Lim ; Ming-Huei Hsieh ; Shu-Cheng Chang ; Hsiu-Han Liao</i>	
2.7 - 8-LAYERS 3D VERTICAL RRAM WITH EXCELLENT SCALABILITY TOWARDS STORAGE CLASS MEMORY APPLICATIONS.....	48
<i>Qing Luo ; Xiaoxin Xu ; Tiancheng Gong ; Hangbing Lv ; Danian Dong ; Haili Ma ; Peng Yuan ; Jianfeng Gao ; Jing Liu ; Zhaoan Yu ; Junfeng Li ; Shibing Long ; Qi Liu ; Ming Liu</i>	
3.1 - 3D SEQUENTIAL INTEGRATION: APPLICATION-DRIVEN TECHNOLOGICAL ACHIEVEMENTS AND GUIDELINES.....	52
<i>P. Batude ; L. Brunet ; C. Fenouillet-Beranger ; F. Andrieu ; J. -P. Colinge ; D. Lattard ; E. Vianello ; S. Thuries ; O. Billoint ; P. Vivet ; C. Santos ; B. Mathieu ; B. Sklenard ; C. -M. V. Lu ; J. Micout ; F. Deprat ; E. Avelar Mercado ; F. Ponthenier ; N. Rambal ; M. -P. Samson ; M. Cassé ; S. Hentz ; J. Arcamone ; G. Sicard ; L. Hutin ; L. Pasini ; A. Ayres ; O. Rozeau ; R. Berthelon ; F. Nemouchi ; P. Rodriguez ; J. -B. Pin ; D. Larmagnac ; A. Duboust ; V. Ripoche ; S. Barraud ; N. Allouti ; S. Barnola ; C. Vizios ; J. -M. Hartmann ; S. Kerdiles ; P. Acosta Alba ; S. Beaupaire ; V. Beugin ; F. Fournel ; P. Besson ; V. Loup ; R. Gassilloud ; F. Martin ; X. Garros ; F. Mazen ; B. Previtali ; C. Euvrard-Colnat ; V. Balan ; C. Comboroure ; M. Zussy ; Mazzocchi ; O. Faynot ; M. Vinet</i>	
3.2 - PIXEL/DRAM/LOGIC 3-LAYER STACKED CMOS IMAGE SENSOR TECHNOLOGY.....	56
<i>H. Tsugawa ; H. Takahashi ; R. Nakamura ; T. Umebayashi ; T. Ogita ; H. Okano ; K. Iwase ; H. Kawashima ; T. Yamasaki ; D. Yoneyama ; J. Hashizume ; T. Nakajima ; K. Murata ; Y. Kanaishi ; K. Ikeda ; K. Tatani ; T. Nagano ; H. Nakayama ; T. Haruta ; T. Nomoto</i>	
3.3 - POWER INSIDE — APPLICATIONS AND TECHNOLOGIES FOR INTEGRATED POWER IN MICROELECTRONICS.....	60
<i>C. Ó Mathúna ; S. Kulkarni ; Z. Pavlovic ; D. Casey ; J. Rohan ; A. -M. Kelleher ; G. Maxwell ; J. O'Brien ; P. McCloskey</i>	
3.4 - 3D SYSTEM PACKAGE ARCHITECTURE AS ALTERNATIVE TO 3D STACKING OF ICs WITH TSV AT SYSTEM LEVEL.....	64
<i>Rao R. Tummala</i>	

3.5 - ADVANCED PACKAGING SAVES THE DAY! — HOW TSV TECHNOLOGY WILL ENABLE CONTINUED SCALING	67
<i>L. England ; I. Arsovski</i>	
3.6 - ADVANCED PACKAGING WITH GREATER SIMPLICITY	71
<i>Douglas C. H. Yu</i>	
3.7 - TOWARDS CUBE-SIZED COMPUTE NODES: ADVANCED PACKAGING CONCEPTS ENABLING EXTREME 3D INTEGRATION	75
<i>T. Brunschwiler ; G. Schlottig ; A. Sridhar ; P. Bezerra ; P. Ruch ; N. Ebejer ; H. Oppermann ; J. Kleff ; W. Steller ; M. Jatlaoui ; F. Voiron ; Z. Pavlovic ; P. McCloskey ; D. Bremner ; P. Parida ; F. Krismer ; J. Kolar ; B. Michel</i>	
4.1 - ATOMISTIC INVESTIGATION OF THE ELECTRONIC STRUCTURE, THERMAL PROPERTIES AND CONDUCTION DEFECTS IN GE-RICH Ge_xSe_{1-x} MATERIALS FOR SELECTOR APPLICATIONS	79
<i>S. Clima ; B. Govoreanu ; K. Opsomer ; A. Velea ; N. S. Avasarala ; W. Devulder ; I. Shlyakhov ; G. L. Donadio ; T. Witters ; S. Kundu ; L. Goux ; V. Afanasiev ; G. S. Kar ; G. Pourtois</i>	
4.2 - AB-INITIO MODELING OF CBRAM CELLS: FROM BALLISTIC TRANSPORT PROPERTIES TO ELECTRO-THERMAL EFFECTS	83
<i>F. Ducry ; A. Emboras ; S. Andermatt ; M. H. Bani-Hashemian ; B. Cheng ; J. Leuthold ; M. Luisier</i>	
4.3 - FUNDAMENTAL MECHANISM BEHIND VOLATILE AND NON-VOLATILE SWITCHING IN METALLIC CONDUCTING BRIDGE RAM	87
<i>Nikhil Shukla ; Ram Krishna Ghosh ; Benjamin Grisafe ; Suman Datta</i>	
4.4 - MODELING DISORDER EFFECT OF THE OXYGEN VACANCY DISTRIBUTION IN FILAMENTARY ANALOG RRAM FOR NEUROMORPHIC COMPUTING	91
<i>Bin Gao ; Huaqiang Wu ; Wei Wu ; Xiaohu Wang ; Peng Yao ; Yue Xi ; Wenqiang Zhang ; Ning Deng ; Peng Huang ; Xiaoyan Liu ; Jinfeng Kang ; Hong-Yu Chen ; Shimeng Yu ; He Qian</i>	
4.5 - COMPREHENSIVE INVESTIGATIONS ON CHARGE DIFFUSION PHYSICS IN SIN- BASED 3D NAND FLASH MEMORY THROUGH SYSTEMATICAL AB INITIO CALCULATIONS	95
<i>Jixuan Wu ; Dan Han ; Wenjing Yang ; Shiyu Chen ; Xiangwei Jiang ; Jiezhong Chen</i>	
4.6 - A PHYSICS-BASED QUASI-2D MODEL TO UNDERSTAND THE WORDLINE (WL) INTERFERENCE EFFECTS OF JUNCTION-FREE STRUCTURE OF 3D NAND AND EXPERIMENTAL STUDY IN A 3D NAND FLASH TEST CHIP	99
<i>Wei-Chen Chen ; Hang-Ting Lue ; Chih-Chang Hsieh ; Yung-Chun Lee ; Pei-Ying Du ; Tzu-Hsuan Hsu ; Kuo-Pin Chang ; Keh-Chung Wang ; Chih-Yuan Lu</i>	
4.7 - TEMPERATURE ACTIVATION OF THE STRING CURRENT AND ITS VARIABILITY IN 3-D NAND FLASH ARRAYS	103
<i>D. Resnati ; A. Mannara ; G. Nicosia ; G. M. Paolucci ; P. Tessariol ; A. L. Lacaita ; A. S. Spinelli ; C. Monzio Compagnoni</i>	
5.1 - GATE-TUNABLE MEMRISTORS FROM MONOLAYER MOS2	107
<i>Vinod K. Sangwan ; Hong-Sub Lee ; Mark C. Hersam</i>	
5.2 - FIRST DEMONSTRATION OF HIGH PERFORMANCE 2D MONOLAYER TRANSISTORS ON PAPER SUBSTRATES	111
<i>Saungeun Park ; Deji Akinwande</i>	
5.3 - ROOM TEMPERATURE 2D MEMRISTIVE TRANSISTOR WITH OPTICAL SHORT-TERM PLASTICITY	115
<i>Xuejun Xie ; Jiahao Kang ; Yongji Gong ; Pulickel M. Ajayan ; Kaustav Banerjee</i>	
5.4 - COEXISTENCE OF VOLATILE AND NON-VOLATILE RESISTIVE SWITCHING IN 2D H- BN BASED ELECTRONIC SYNAPSES	119
<i>Y. Shi ; C. Pan ; V. Chen ; N. Raghavan ; K. L. Pey ; F. M. Puglisi ; E. Pop ; H. -S. P. Wong ; M. Lanza</i>	
5.5 - SCALING CARBON NANOTUBE CMOS FETS TOWARDS QUANTUM LIMIT	123
<i>Chenguang Qiu ; Zhiyong Zhang ; Lian-Mao Peng</i>	
5.6 - SOLUTION-PROCESSED CARBON NANOTUBES BASED TRANSISTORS WITH CURRENT DENSITY OF 1.7 MA/μM AND PEAK TRANSCONDUCTANCE OF 0.8 MS/μM	127
<i>Donglai Zhong ; Mengmeng Xiao ; Zhiyong Zhang ; Lian-Mao Peng</i>	
5.7 - BENCHMARKING OF MONOLITHIC 3D INTEGRATED MX2 FETS WITH SI FINFETS	131
<i>T. Agarwal ; A. Szabo ; M. G. Bardon ; B. Soree ; I. Radu ; P. Raghavan ; M. Luisier ; W. Dehaene ; M. Heyns</i>	
6.1 - NEUROSIM+: AN INTEGRATED DEVICE-TO-ALGORITHM FRAMEWORK FOR BENCHMARKING SYNAPTIC DEVICES AND ARRAY ARCHITECTURES	135
<i>Pai-Yu Chen ; Xiaochen Peng ; Shimeng Yu</i>	
6.2 - FERROELECTRIC FET ANALOG SYNAPSE FOR ACCELERATION OF DEEP NEURAL NETWORK TRAINING	139
<i>Matthew Jerry ; Pai-Yu Chen ; Jianchi Zhang ; Pankaj Sharma ; Kai Ni ; Shimeng Yu ; Suman Datta</i>	

6.3 - RANDOM SPARSE ADAPTATION FOR ACCURATE INFERENCE WITH INACCURATE MULTI-LEVEL RRAM ARRAYS	143
<i>Abinash Mohanty ; Xiacong Du ; Pai-Yu Chen ; Jae-Sun Seo ; Shimeng Yu ; Yu Cao</i>	
6.4 - TIME-DEPENDENT VARIABILITY IN RRAM-BASED ANALOG NEUROMORPHIC SYSTEM FOR PATTERN RECOGNITION	147
<i>Jian Kang ; Zhizhen Yu ; Lindong Wu ; Yichen Fang ; Zongwei Wang ; Yimao Cai ; Zhigang Ji ; Jianfu Zhang ; Runsheng Wang ; Yuchao Yang ; Ru Huang</i>	
6.5 - FAST, ENERGY-EFFICIENT, ROBUST, AND REPRODUCIBLE MIXED-SIGNAL NEUROMORPHIC CLASSIFIER BASED ON EMBEDDED NOR FLASH MEMORY TECHNOLOGY	151
<i>X. Guo ; F. Merrikh Bayat ; M. Bavandpour ; M. Klachko ; M. R. Mahmoodi ; M. Prezioso ; K. K. Likharev ; D. B. Strukov</i>	
6.6 - DESIGN GUIDELINES OF STOCHASTIC COMPUTING BASED ON FINFET: A TECHNOLOGY-CIRCUIT PERSPECTIVE	155
<i>Yaven Zhang ; Runsheng Wang ; Xiaobo Jiang ; Zhenghan Lin ; Shaofeng Guo ; Zhe Zhang ; Zherui Zhang ; Ru Huang</i>	
7.1 - COMPLETE DEGRADATION MAPPING OF STACKED GATE-ALL-AROUND SI NANOWIRE TRANSISTORS CONSIDERING BOTH INTRINSIC AND EXTRINSIC EFFECTS	159
<i>Adrian Chasin ; Erik Bury ; Ben Kaczer ; Jacopo Franco ; Philippe Roussel ; Romain Ritzenhaller ; Hans Mertens ; Naoto Horiguchi ; Dimitri Linten ; Anda Mocuta</i>	
7.2 - NEW INSIGHTS INTO THE HOT CARRIER DEGRADATION (HCD) IN FINFET: NEW OBSERVATIONS, UNIFIED COMPACT MODEL, AND IMPACTS ON CIRCUIT RELIABILITY	163
<i>Zhuoqing Yu ; Jiayang Zhang ; Runsheng Wang ; Shaofeng Guo ; Changze Liu ; Ru Huang</i>	
7.3 - MODELING OF NBTI TIME KINETICS AND T DEPENDENCE OF VAF IN SIGE P-FINFETS	167
<i>N. Parihar ; R. Southwick ; M. Wang ; J. H. Stathis ; S. Mahapatra</i>	
7.4 - TOWARDS OPTIMAL ESD DIODES IN NEXT GENERATION BULK FINFET AND GAA NW TECHNOLOGY NODES	171
<i>S. -H. Chen ; G. Hellings ; D. Linten ; T. Chiarella ; H. Mertens ; R. Boschke ; J. Mitard ; S. Kubicek ; R. Ritzenhaller ; E. Bury ; N. Wang ; G. Groeseneken ; A. Mocuta ; N. Horiguchi</i>	
7.5 - CHARACTERIZATION OF OXIDE DEFECTS IN INGAAS MOS GATE STACKS FOR HIGH-MOBILITY N-CHANNEL MOSFETS (INVITED)	175
<i>J. Franco ; V. Putcha ; A. Vais ; S. Sioncke ; N. Waldron ; D. Zhou ; G. Rzepa ; Ph. J. Roussel ; G. Groeseneken ; M. Heyns ; N. Collaert ; D. Linten ; T. Grassler ; B. Kaczer</i>	
7.6 - THERMAL EFFECTS IN 3D SEQUENTIAL TECHNOLOGY	179
<i>K. Triantopoulos ; M. Cassé ; L. Brunet ; P. Batude ; C. Fenouillet-Béranger ; B. Mathieu ; M. Vinet ; G. Ghibaudo ; G. Reimbold</i>	
8.1 - FLEXIBLE CMOS ELECTRONICS BASED ON P-TYPE $Ge_2Sb_2Te_5$ AND N-TYPE $InGaZnO_4$ SEMICONDUCTORS	183
<i>A. Daus ; S. Han ; S. Knobelspies ; G. Cantarella ; C. Vogt ; N. Münzenrieder ; G. Tröster</i>	
8.2 - HIGHLY ROBUST OXIDE THIN FILM TRANSISTORS WITH SPLIT ACTIVE SEMICONDUCTOR AND SOURCE/DRAIN ELECTRODES	187
<i>Suhui Lee ; Di Geng ; Ling Li ; Ming Liu ; Jin Jang</i>	
8.3 - MANUFACTURED-ON-DEMAND STEEP SUBTHRESHOLD ORGANIC FIELD EFFECT TRANSISTOR FOR LOW POWER AND HIGH SENSITIVITY ION AND FLUORESCENCE SENSING	191
<i>J. Zhao ; Q. Li ; Y. Huang ; S. Li ; W. Tang ; S. Peng ; S. Chen ; W. Liu ; X. Guo</i>	
8.4 - BLACK PHOSPHORUS CARBIDE INFRARED PHOTOTRANSISTOR WITH WIDE SPECTRUM SENSING FOR IOT APPLICATIONS	195
<i>Wee Chong Tan ; Li Huang ; Rui Jie Ng ; Lin Wang ; Kah-Wee Ang</i>	
8.5 - THERMALLY STABLE AND FLEXIBLE PAPER PHOTOSENSORS BASED ON 2D BN NANOSHEETS	199
<i>C. H. Lin ; B. Cheng ; M. L. Tsai ; H. C. Fu ; W. Luo ; L. H. Zhou ; S. H. Jang ; L. B. Hu ; J. H. He</i>	
8.6 - HIGH-PERFORMANCE, FLEXIBLE GRAPHENE/ULTRA-THIN SILICON ULTRA-VIOLET IMAGE SENSOR	203
<i>Ayaz Ali ; Khurram Shehzad ; Hongwei Guo ; Zhen Wang ; Peng Wang ; Akeel Qadir ; Weida Hu ; Tianling Ren ; Bin Yu ; Yang Xu</i>	
8.7 - GRAPHENE/SILICON-QUANTUM-DOTS/SI SCHOTTKY-PN CASCADE HETEROJUNCTION FOR SHORT-WAVELENGTH INFRARED PHOTODETECTION	207
<i>Sichao Du ; Zhenyi Ni ; Xuemei Liu ; Hongwei Guo ; Ayaz Ali ; Yang Xu ; Xiaodong Pi</i>	

9.1 - BODY PIN DIODE INACTIVATION WITH LOW ON-RESISTANCE ACHIEVED BY A 1.2 KV-CLASS 4H-SIC SWITCH-MOS	211
<i>Yusuke Kobayashi ; Naoyuki Ohse ; Tadao Morimoto ; Makoto Kato ; Takahito Kojima ; Masaki Miyazato ; Manabu Takei ; Hiroshi Kimura ; Shinsuke Harada</i>	
9.2 - 1200 V GAN VERTICAL FIN POWER FIELD-EFFECT TRANSISTORS	215
<i>Y. Zhang ; M. Sun ; D. Piedra ; J. Hu ; Z. Liu ; Y. Lin ; X. Gao ; K. Shepard ; T. Palacios</i>	
9.3 - DETERMINATION OF INTRINSIC PHONON-LIMITED MOBILITY AND CARRIER TRANSPORT PROPERTY EXTRACTION OF 4H-SIC MOSFETS	219
<i>M. Noguchi ; T. Iwamatsu ; H. Amishiro ; H. Watanabe ; K. Kita ; S. Yamakawa</i>	
9.4 - DEMONSTRATING >1.4 KV OG-FET PERFORMANCE WITH A NOVEL DOUBLE FIELD-PLATED GEOMETRY AND THE SUCCESSFUL SCALING OF LARGE-AREA DEVICES	223
<i>Dong Ji ; Chirag Gupta ; Silvia H. Chan ; Anchal Agarwal ; Wenwen Li ; Stacia Keller ; Umesh K. Mishra ; Srabanti Chowdhury</i>	
9.5 - PROGRESS AND FUTURE CHALLENGES OF SIC POWER DEVICES AND PROCESS TECHNOLOGY	227
<i>T. Kimoto ; H. Niwa ; N. Kaji ; T. Kobayashi ; Y. Zhao ; S. Mori ; M. Aketa</i>	
9.6 - HIGH VOLTAGE VERTICAL P-N DIODES WITH ION-IMPLANTED EDGE TERMINATION AND SPUTTERED SINX PASSIVATION ON GAN SUBSTRATES	231
<i>Jingshan Wang ; Lina Cao ; Jinqiao Xie ; Edward Beam ; Robert McCarthy ; Chris Youtsey ; Patrick Fay</i>	
10.2 - DEVELOPMENT OF HIGH-FREQUENCY BULK ACOUSTIC WAVE (BAW) RESONATORS AS BIOSENSORS AND BIOACTUATORS	235
<i>X. Duan ; S. Pan ; W. Pang</i>	
10.3 - A SINGLE BACTERIUM AND MAMMALIAN CELL ANALYSIS BY IONIC CURRENT MEASUREMENTS IN A MICROCHANNEL	239
<i>N. Kaji ; M. Sano ; S. Ito ; H. Yasaki ; T. Yasui ; H. Yukawa ; Y. Baba</i>	
10.4 - RAPID ANTIBIOTIC SUSCEPTIBILITY TESTING SYSTEM: LIFE SAVING BIOMEMS DEVICES	243
<i>H. Y. Jeong ; E. -G. Kim ; S. Han ; G. Y. Lee ; S. Han ; B. Jin ; T. Lim ; H. C. Kim ; T. S. Kim ; D. Y. Kim ; S. Kwon</i>	
10.5 - MICROSCALE PROFILING OF CIRCULATING TUMOR CELLS	247
<i>Reza Mohamadi ; Shana Kelley</i>	
10.6 - ENCAPSULATED ORGANIDS & ORGAN-ON-A-CHIP PLATFORM FOR CANCER MODELING	251
<i>N. Piccollet-D'Hahan ; B. Laperrousaz ; S. Porte ; P. Obeid ; A. Tollance ; F. Kermarrec ; C. Belda-Marin ; A. Romero-Millan ; V. Haguet ; D. K. Martin ; X. Gidrol</i>	
10.7 - TISSUE MICROENVIRONMENT AND CELLULAR IMAGING	255
<i>S. S. Nasserri ; S. M. Grist ; S. Chen ; Y. Y. Tam ; P. Cullis ; K. C. Cheung</i>	
11.1 - STOCHASTIC SYNAPSES AS RESOURCE FOR EFFICIENT DEEP LEARNING MACHINES	259
<i>Emre Neftci</i>	
11.2 - ATTRACTOR NETWORKS AND ASSOCIATIVE MEMORIES WITH STDP LEARNING IN RRAM SYNAPSES	263
<i>V. Milo ; D. Ielmini ; E. Chicca</i>	
11.3 - ENERGY USE CONSTRAINS BRAIN INFORMATION PROCESSING	267
<i>Mireille Conrad ; Elisabeth Engl ; Renaud B. Jolivet</i>	
11.4 - UNDERSTANDING THE TRADE-OFFS OF DEVICE, CIRCUIT AND APPLICATION IN RERAM-BASED NEUROMORPHIC COMPUTING SYSTEMS	270
<i>Bonan Yan ; Chenchen Liu ; Xiaoxiao Liu ; Yiran Chen ; Hai Li</i>	
11.5 - DEVICE AND CIRCUIT OPTIMIZATION OF RRAM FOR NEUROMORPHIC COMPUTING	274
<i>Huaqiang Wu ; Peng Yao ; Bin Gao ; Wei Wu ; Qingtian Zhang ; Wenqiang Zhang ; Ning Deng ; Dong Wu ; H. - S. Philip Wong ; Shimeng Yu ; He Qian</i>	
11.6 - CHALLENGES AND OPPORTUNITIES TOWARD ONLINE TRAINING ACCELERATION USING RRAM-BASED HARDWARE NEURAL NETWORK	278
<i>Chih-Cheng Chang ; Jen-Chieh Liu ; Yu-Lin Shen ; Teyuh Chou ; Pin-Chun Chen ; I. -Ting Wang ; Chih-Chun Su ; Ming-Hong Wu ; Boris Hudec ; Che-Chia Chang ; Chia-Ming Tsai ; Tian-Sheuan Chang ; H. -S. Philip Wong ; Tuo-Hung Hou</i>	
11.7 - MULTISCALE MODELING OF NEUROMORPHIC COMPUTING: FROM MATERIALS TO DEVICE OPERATIONS	282
<i>Luca Larcher ; Andrea Padovani ; Valerio Di Lecce</i>	
12.1 - TWIN MODE NV LOGIC GATES FOR HIGH SPEED COMPUTING SYSTEM ON 16NM FINFET CMOS LOGIC PROCESS	286
<i>Wei-Yu Chien ; Tai-Min Wang ; Yue-Der Chih ; Jonathan Chang ; Chrong Jung Lin ; Ya-Chin King</i>	

12.2 - A NOVEL PUF AGAINST MACHINE LEARNING ATTACK: IMPLEMENTATION ON A 16 MB RRAM CHIP	290
<i>Yachuan Pang ; Huaqiang Wu ; Bin Gao ; Dong Wu ; An Chen ; He Qian</i>	
12.3 - LARGE-SCALE TERAHERTZ ACTIVE ARRAYS IN SILICON USING HIGHLY-VERSATILE ELECTROMAGNETIC STRUCTURES	294
<i>Cheng Wang ; Zhi Hu ; G. Zhang ; J. Holloway ; Ruonan Han</i>	
12.4 - VARIABILITY-AND RELIABILITY-AWARE DESIGN FOR 16/14NM AND BEYOND TECHNOLOGY	298
<i>R. Huang ; X. B. Jiang ; S. F. Guo ; P. P. Ren ; P. Hao ; Z. Q. Yu ; Z. Zhang ; Y. Y. Wang ; R. S. Wang</i>	
12.5 - A NOVEL BIT-LEVEL CHARACTERIZATION METHODOLOGY TO BENCHMARK THE FINFET BASED SRAM PERFORMANCE UNDER THE INFLUENCE OF LEAKAGE CURRENT	302
<i>J. C. Liu ; S. Mukhopadhyay ; Y. F. Wang ; Y. S. Tsai ; S. C. Chen ; J. H. Lee ; Ryan Lu ; Y. -H. Lee ; Jun He</i>	
12.6 - TSV-FREE FINFET-BASED MONOLITHIC 3D+IC WITH COMPUTING-IN-MEMORY SRAM CELL FOR INTELLIGENT IOT DEVICES	306
<i>Fu-Kuo Hsueh ; Hsiao-Yun Chiu ; Chang-Hong Shen ; Jia-Min Shieh ; Ying-Tsan Tang ; Chih-Chao Yang ; Hsiu-Chih Chen ; Wen-Hsien Huang ; Bo-Yuan Chen ; Kun-Ming Chen ; Guo-Wei Huang ; Wei-Hao Chen ; Kuo-Hsiang Hsu ; Srivatsa Rangachar Srinivasa ; Nicholas Jao ; Albert Lee ; Hochul Lee ; Vijaykrishnan Narayanan ; Kang-Lung Wang ; Meng-Fan Chang ; Wen-Kuan Yeh</i>	
13.1 - HOT-CARRIER DEGRADATION IN FINFETS: MODELING, PECULIARITIES, AND IMPACT OF DEVICE TOPOLOGY	310
<i>A. Makarov ; S. E. Tyaginov ; B. Kaczer ; M. Jech ; A. Chasin ; A. Grill ; G. Hellings ; M. I. Vexler ; D. Linten ; T. Grasser</i>	
13.2 - PERFORMANCE COMPARISON FOR FINFETS, NANOWIRE AND STACKED NANOWIRE FETS: FOCUS ON THE INFLUENCE OF SURFACE ROUGHNESS AND THERMAL EFFECTS	314
<i>O. Badami ; F. Driussi ; P. Palestri ; L. Selmi ; D. Esseni</i>	
13.3 - MONTE CARLO BENCHMARK OF $\text{In}_{0.53}\text{Ga}_{0.47}\text{As}$-AND SILICON-FINFETS	318
<i>F. M. Bufler ; G. Eneman ; N. Collaert ; A. Mocuta</i>	
13.4 - MODELLING NANOSCALE N-MOSFETS WITH III-V COMPOUND SEMICONDUCTOR CHANNELS: FROM ADVANCED MODELS FOR BAND STRUCTURES, ELECTROSTATICS AND TRANSPORT TO TCAD	322
<i>L. Selmi ; E. Caruso ; S. Carapezzi ; M. Visciarelli ; E. Gnani ; N. Zagni ; P. Pavan ; P. Palestri ; D. Esseni ; A. Gnudi ; S. Reggiani ; F. M. Puglisi ; G. Verzellesi</i>	
13.5 - FERROELECTRIC TRANSISTOR MODEL BASED ON SELF-CONSISTENT SOLUTION OF 2D POISSON'S, NON-EQUILIBRIUM GREEN'S FUNCTION AND MULTI-DOMAIN LANDAU KHALATNIKOV EQUATIONS	326
<i>A. K. Saha ; P. Sharma ; I. Dabo ; S. Datta ; S. K. Gupta</i>	
13.6 - A NEW FRAMEWORK OF PHYSICS-BASED COMPACT MODEL PREDICTS RELIABILITY OF SELF-HEATED MODERN ICS: FINFET, NWFET, NSHFET COMPARISON	330
<i>Woojin Ahn ; Chunsheng Jiang ; Jun Xu ; Muhammad Ashrafal Alam</i>	
14.1 - 20 YEARS OF CU BEOL IN MANUFACTURING, AND ITS FUTURE PROSPECTS	334
<i>Daniel C. Edelstein</i>	
14.2 - FULLY ALIGNED VIA INTEGRATION FOR EXTENDIBILITY OF INTERCONNECTS TO BEYOND THE 7 NM NODE	338
<i>Benjamin D. Briggs ; C. B. Peethala ; D. L. Rath ; J. Lee ; S. Nguyen ; N. V. Licausi ; P. S. McLaughlin ; H. You ; D. Sil ; N. A. Lanzillo ; H. Huang ; R. Patlolla ; T. Haigh ; Y. Xu ; C. Park ; P. Kerber ; H. K. Shobha ; Y. Kim ; J. Demarest ; J. Li ; G. Lian ; M. Ali ; C. T. Le ; E. T. Ryan ; L. A. Clevenger ; D. F. Canaperi ; T. E. Standaert ; G. Bonilla ; E. Huang</i>	
14.3 - ALL-CARBON INTERCONNECT SCHEME INTEGRATING GRAPHENE-WIRES AND CARBON-NANOTUBE-VIAS	342
<i>Junkai Jiang ; Jiahao Kang ; Jae Hwan Chu ; Kaustav Banerjee</i>	
14.4 - CONTINUING MOORE'S LAW WITH EUV LITHOGRAPHY	346
<i>B. Turkot ; S. Carson ; A. Lio</i>	
14.5 - ELECTRON BEAM DETECTION OF COBALT TRENCH EMBEDDED VOIDS ENABLING IMPROVED PROCESS CONTROL FOR MIDDLE-OF-LINE AT THE 7NM NODE AND BEYOND	349
<i>N. Breil ; D. Shemesh ; J. Fernandez ; R. Hung ; N. Bekiaris ; J. Tseng ; M. Naik ; J. H. Park ; J. Bakke ; A. Kumar ; K. Nafisi ; A. Litman ; A. Karnieli ; V. Kuchik ; A. Wachs ; N. Khasgiwale ; M. Chudzick</i>	
14.6 - IMPROVEMENT OF HFO₂ BASED RRAM ARRAY PERFORMANCES BY LOCAL SI IMPLANTATION	353
<i>M. Barlas ; A. Grossi ; L. Grenouillet ; E. Vianello ; E. Nolot ; N. Vaxelaire ; P. Blaise ; B. Traoré ; J. Coignus ; F. Perrin ; R. Crochemore ; F. Mazen ; L. Lachal ; S. Pauliac ; C. Pellissier ; S. Bernasconi ; S. Chevalliez ; J. F. Nodin ; L. Perniola ; E. Nowak</i>	

15.1 - 14NM FERROELECTRIC FINFET TECHNOLOGY WITH STEEP SUBTHRESHOLD SLOPE FOR ULTRA LOW POWER APPLICATIONS	357
<i>Z. Krivokapic ; U. Rana ; R. Galatage ; A. Razavieh ; A. Aziz ; J. Liu ; J. Shi ; H. J. Kim ; R. Sporer ; C. Serrao ; A. Busquet ; P. Polakowski ; J. Müller ; W. Kleemeier ; A. Jacob ; D. Brown ; A. Knorr ; R. Carter ; S. Banna</i>	
15.2 - PERSPECTIVE OF NEGATIVE CAPACITANCE FINFETS INVESTIGATED BY TRANSIENT TCAD SIMULATION	361
<i>Hiroyuki Ota ; Koichi Fukuda ; Tsutomu Ikegami ; Junichi Hattori ; Hidehiro Asai ; Shinji Migita ; Akira Toriumi</i>	
15.3 - HYSTERESIS-FREE NEGATIVE CAPACITANCE GERMANIUM CMOS FINFETS WITH BI-DIRECTIONAL SUB-60 MV/DEC	365
<i>Wonil Chung ; Mengwei Si ; Peide D. Ye</i>	
15.4 - GE NANOWIRE FETS WITH HFZROX FERROELECTRIC GATE STACK EXHIBITING SS OF SUB-60 MV/DEC AND BIASING EFFECTS ON FERROELECTRIC RELIABILITY	369
<i>C. -J. Su ; T. -C. Hong ; Y. -C. Tsou ; F. -J. Hou ; P. -J. Sung ; M. -S. Yeh ; C. -C. Wan ; K. -H. Kao ; Y. -T. Tang ; C. -H. Chiu ; C. -J. Wang ; S. -T. Chung ; T. -Y. You ; Y. -C. Huang ; C. -T. Wu ; K. -L. Lin ; G. -L. Luo ; K. -P. Huang ; Y. -J. Lee ; T. -S. Chao ; W. -F. Wu ; G. -W. Huang ; J. -M. Shieh ; W. -K. Yeh ; Y. -H. Wang</i>	
15.5 - FREQUENCY DEPENDENCE OF PERFORMANCE IN GE NEGATIVE CAPACITANCE PFETS ACHIEVING SUB-30 MV/DECADE SWING AND 110 MV HYSTERESIS AT MHZ	373
<i>Jiuren Zhou ; Jibao Wu ; Genquan Han ; Ruoying Kanyang ; Yue Peng ; Jing Li ; Hongjuan Wang ; Yan Liu ; Jincheng Zhang ; Qing-Qing Sun ; David Wei Zhang ; Yue Hao</i>	
15.6 - PROPOSAL AND DEMONSTRATION OF OXIDE-SEMICONDUCTOR/(SI, SIGE, GE) BILAYER TUNNELING FIELD EFFECT TRANSISTOR WITH TYPE-II ENERGY BAND ALIGNMENT	377
<i>K. Kato ; H. Matsui ; H. Tabata ; M. Takenaka ; S. Takagi</i>	
15.7 - CRYSTAL-ORIENTED BLACK PHOSPHORUS TFETS WITH STRONG BAND-TO-BAND-TUNNELING ANISOTROPY AND SUBTHRESHOLD SLOPE NEARING THE THERMIONIC LIMIT	381
<i>Matthew C. Robbins ; Steven J. Koester</i>	
16.1 - AN EXPERIMENTAL CMOS PHOTON DETECTOR WITH 0.5E-RMS TEMPORAL NOISE AND 15μM PITCH ACTIVE SENSOR PIXELS	385
<i>T. Nishihara ; M. Matsumura ; T. Imoto ; K. Okumura ; Y. Sakano ; Y. Yorikado ; Y. Tashiro ; H. Wakabayashi ; Y. Oike ; Y. Nitta</i>	
16.2 - SOI MONOLITHIC PIXEL TECHNOLOGY FOR RADIATION IMAGE SENSOR	389
<i>Y. Arai ; T. Miyoshi ; I. Kurachi</i>	
16.3 - BACK-SIDE ILLUMINATED GESN PHOTODIODE ARRAY ON QUARTZ SUBSTRATE FABRICATED BY LASER-INDUCED LIQUID-PHASE CRYSTALLIZATION FOR MONOLITHICALLY-INTEGRATED NIR IMAGER CHIP	393
<i>H. Oka ; K. Inoue ; T. T. Nguyen ; S. Kuroki ; T. Hosoi ; T. Shimura ; H. Watanabe</i>	
16.4 - NEAR-INFRARED SENSITIVITY ENHANCEMENT OF A BACK-ILLUMINATED COMPLEMENTARY METAL OXIDE SEMICONDUCTOR IMAGE SENSOR WITH A PYRAMID SURFACE FOR DIFFRACTION STRUCTURE	397
<i>I. Oshiyama ; S. Yokogawa ; H. Ikeda ; Y. Ebiko ; T. Hirano ; S. Saito ; T. Oinoue ; Y. Hagimoto ; H. Iwamoto</i>	
16.5 - INDUSTRIALISED SPAD IN 40 NM TECHNOLOGY	401
<i>S. Pellegrini ; B. Rae ; A. Pingault ; D. Golanski ; S. Jouan ; C. Lapeyre ; B. Mamdy</i>	
16.6 - A BACK-ILLUMINATED 3D-STACKED SINGLE-PHOTON AVALANCHE DIODE IN 45NM CMOS TECHNOLOGY	405
<i>M. -J. Lee ; A. R. Ximenes ; P. Padmanabhan ; T. J. Wang ; K. C. Huang ; Y. Yamashita ; D. N. Young ; E. Charbon</i>	
17.1 - RECORD PERFORMANCE TOP-DOWN IN0.53GA0.47AS VERTICAL NANOWIRE FETS AND VERTICAL NANOSHEETS	409
<i>S. Ramesh ; Ts. Ivanov ; V. Putcha ; A. Alian ; A. Sibaja-Hernandez ; R. Rooyackers ; E. Camerotto ; A. Milenin ; N. Pinna ; S. El Kazzi ; A. Veloso ; D. Lin ; P. Lagrain ; P. Favia ; N. Collaert ; K. De Meyer</i>	
17.2 - SUB-10 NM DIAMETER INGAAS VERTICAL NANOWIRE MOSFETS	413
<i>X. Zhao ; C. Heidelberger ; E. A. Fitzgerald ; W. Lu ; A. Vardi ; J. A. Del Alamo</i>	
17.3 - SUB-100-NM GATE-LENGTH SCALING OF VERTICAL INAS/INGAAS NANOWIRE MOSFETS ON SI	417
<i>Olli-Pekka Kilpi ; Johannes Svensson ; Lars-Erik Wernersson</i>	
17.4 - HIGH MOBILITY IN0.30GA0.70AS MOSHEMTS ON LOW THREADING DISLOCATION DENSITY 200 MM SI SUBSTRATES: A TECHNOLOGY ENABLER TOWARDS HETEROGENEOUS INTEGRATION OF LOW NOISE AND MEDIUM POWER AMPLIFIERS WITH SI CMOS	421
<i>Sachin Yadav ; Annie Kumar ; Xuan Sang Nguyen ; Kwang Hong Lee ; Zhihong Liu ; Weichuan Xing ; Saeid Masudy-Panah ; Kenneth Lee ; Chuan Seng Tan ; Eugene A. Fitzgerald ; Dimitri A. Antoniadis ; Yee-Chia Yeo ; Xiao Gong</i>	

17.5 - A SCALED REPLACEMENT METAL GATE INGAAS-ON-INSULATOR N-FINFET ON SI WITH RECORD PERFORMANCE	425
<i>H. Hahn ; V. Deshpande ; E. Caruso ; S. Sant ; E. O'Connor ; Y. Baumgartner ; M. Sousa ; D. Caimi ; A. Olziersky ; P. Palestri ; L. Selmi ; A. Schenk ; L. Czornomaz</i>	
17.6 - SELF-ALIGNED INGAAS FINFETS WITH 5-NM FIN-WIDTH AND 5-NM GATE-CONTACT SEPARATION	429
<i>Alon Vardi ; Lisa Kong ; Wenjie Lu ; Xiaowei Cai ; Xin Zhao ; Jesús Grajal ; Jesús A. Del Alamo</i>	
17.7 - 10-NM FIN-WIDTH INGASB P-CHANNEL SELF-ALIGNED FINFETS USING ANTIMONIDE-COMPATIBLE DIGITAL ETCH	433
<i>W. Lu ; I. P. Roh ; D. -M. Geum ; S. -H. Kim ; J. D. Song ; L. Kong ; J. A. Del Alamo</i>	
18.1 - LAB ON SKIN™: 3D MONOLITHICALLY INTEGRATED ZERO-ENERGY MICRO/NANOFLUIDICS AND FD SOI ION SENSITIVE FETS FOR WEARABLE MULTI-SENSING SWEAT APPLICATIONS	437
<i>F. Bellando ; E. Garcia-Cordero ; F. Wildhaber ; J. Longo ; H. Guérin ; A. M. Ionescu</i>	
18.2 - SKIN-LIKE NANOSTRUCUTRED BIOSENSOR SYSTEM FOR NONINVASIVE BLOOD GLUCOSE MONITORING	441
<i>Yihao Chen ; Siyuan Lu ; Xue Feng</i>	
18.3 - MECHANICAL-FIELD-COUPLED THIN-FILM TRANSISTOR FOR TACTILE SENSING WITH MN DYNAMIC FORCE DETECTION CAPABILITY AND WEARABLE SELF-DRIVEN HEART RATE MONITORING WITH μW POWER CONSUMPTION	445
<i>Weiwei Li ; Ahmed Rasheed ; Xiao Feng ; Emad Iranmanesh ; Kai Wang ; Hai Ou ; Jun Chen ; Shaozhi Deng ; Ningsheng Xu</i>	
18.4 - ENERGY-EFFICIENT ALL FIBER-BASED LOCAL BODY HEAT MAPPING CIRCUITRY COMBINING THERMISTOR AND MEMRISTOR FOR WEARABLE HEALTHCARE DEVICE	449
<i>Hagyoul Bae ; Weon-Guk Kim ; Hongkeun Park ; Seung-Bae Jeon ; Soo-Ho Jung ; Hye Moon Lee ; Myung-Su Kim ; Il-Woong Tcho ; Byung Chul Jang ; Hwon Im ; Sung-Yool Choi ; Sung Gap Im ; Yang-Kyu Choi</i>	
18.5 - 3D HETEROGENEOUS INTEGRATED MONOLAYER GRAPHENE SI-CMOS RF GAS SENSOR PLATFORM	453
<i>M. Holt ; S. M. Mortazavi Zanjani ; M. M. Sadeghi ; D. Akinwande</i>	
18.6 - TWO-DIMENSIONAL SNS2 FOR DETECTING GASES CAUSING “SICK BUILDING SYNDROME”	457
<i>K. Hayashi ; M. Kataoka ; H. Jippo ; M. Ohfuchi ; T. Iwai ; S. Sato</i>	
19.1 - A 128GB (MLC)/192GB (TLC) SINGLE-GATE VERTICAL CHANNEL (SGVC) ARCHITECTURE 3D NAND USING ONLY 16 LAYERS WITH ROBUST READ DISTURB, LONG-RETENTION AND EXCELLENT SCALING CAPABILITY	461
<i>Hang-Ting Lue ; Pei-Ying Du ; Wei-Chen Chen ; Yung-Chun Lee ; Tzu-Hsuan Hsu ; Teng-Hao Yeh ; Kuo-Pin Chang ; Chih-Chang Hsieh ; Chiatze Huang ; Guan-Ru Lee ; Chih-Ping Chen ; Chieh-Fang Chen ; Chia-Jung Chiu ; Y. J. Chen ; W. P. Lu ; Tahone Yang ; Kuang-Chao Chen ; Chun-Hsiung Hung ; Keh-Chung Wang ; Chih-Yuan Lu</i>	
19.2 - LATERAL CHARGE MIGRATION SUPPRESSION OF 3D-NAND FLASH BY V_{TH} NEARING FOR NEAR DATA COMPUTING	465
<i>Kyoji Mizoguchi ; Shohei Kotaki ; Yoshiaki Deguchi ; Ken Takeuchi</i>	
19.3 - RELIABILITY AND SCALABILITY OF FINFET SPLIT-GATE MONOS ARRAY WITH TIGHT VTH DISTRIBUTION FOR 16/14NM-NODE EMBEDDED FLASH	469
<i>S. Tsuda ; T. Saito ; H. Nagase ; Y. Kawashima ; A. Yoshitomi ; S. Okanishi ; T. Hayashi ; T. Maruyama ; M. Inoue ; S. Muranaka ; S. Kato ; T. Hagiwara ; H. Saito ; T. Yamaguchi ; M. Kadoshima ; T. Maruyama ; T. Mihara ; H. Yanagita ; K. Sonoda ; T. Yamashita ; Y. Yamaguchi</i>	
19.4 - ADVANCED MEMORY SOLUTIONS FOR EMERGING CIRCUITS AND SYSTEMS	473
<i>B. Giraud ; A. Makosiej ; R. Boumchedda ; N. Gupta ; A. Levisse ; E. Vianello ; J. -P. Noel</i>	
19.5 - 2D MOLYBDENUM DISULFIDE (MOS2) TRANSISTORS DRIVING RRAMS WITH 1T1R CONFIGURATION	477
<i>Rui Yang ; Haitong Li ; Kirby K. H. Smithe ; Taeho R. Kim ; Kye Okabe ; Eric Pop ; Jonathan A. Fan ; H. -S. Philip Wong</i>	
19.6 - ENGINEERING OF FERROELECTRIC SWITCHING SPEED IN SI DOPED HFO₂ FOR HIGH-SPEED IT-FERAM APPLICATION	481
<i>H. K. Yoo ; J. S. Kim ; Z. Zhu ; Y. S. Choi ; A. Yoon ; M. R. Macdonald ; X. Lei ; T. Y. Lee ; D. Lee ; S. C. Chae ; J. Park ; D. Hemker ; J. G. Langan ; Y. Nishi ; S. J. Hong</i>	
19.7 - A FEFET BASED SUPER-LOW-POWER ULTRA-FAST EMBEDDED NVM TECHNOLOGY FOR 22NM FDSOI AND BEYOND	485
<i>S. Dünkel ; M. Trentsch ; R. Richter ; P. Möll ; C. Fuchs ; O. Gehring ; M. Majer ; S. Wittek ; B. Müller ; T. Melde ; H. Mulaosmanovic ; S. Slesazek ; S. Müller ; J. Ocker ; M. Noack ; D. -A. Löhr ; P. Polakowski ; J. Müller ; T. Mikolajick ; J. Höntschel ; B. Rice ; J. Pellerin ; S. Beyer</i>	

20.1 - OVERCOMING INTERCONNECT SCALING CHALLENGES USING NOVEL PROCESS AND DESIGN SOLUTIONS TO IMPROVE BOTH HIGH-SPEED AND LOW-POWER COMPUTING MODES	489
<i>Kaushik Vaidyanathan ; Daniel H. Morris ; Uygur E. Avci ; Ishwar S. Bhati ; Lavanya Subramanian ; Jayesh Gaur ; Huichu Liu ; Sreenivas Subramoney ; Tanay Karnik ; Hong Wang ; Ian A. Young</i>	
20.2 - IMPACT OF AGGRESSIVE FIN WIDTH SCALING ON FINFET DEVICE CHARACTERISTICS	493
<i>X. He ; J. Fronheiser ; P. Zhao ; Z. Hu ; S. Uppal ; X. Wu ; Y. Hu ; R. Sporer ; L. Qin ; R. Krishnan ; E. M. Bazizi ; R. Carter ; K. Tabakman ; A. K. Jha ; H. Yu ; O. Hu ; D. Choi ; J. G. Lee ; S. B. Samavedam ; D. K. Sohn</i>	
20.3 - DESIGN TECHNOLOGY CO-OPTIMIZATION OF 3D-MONOLITHIC STANDARD CELLS AND SRAM EXPLOITING DYNAMIC BACK-BIAS FOR ULTRA-LOW-VOLTAGE OPERATION	497
<i>F. Andrieu ; R. Berthelon ; R. Boumchedda ; G. Tricaud ; L. Brunet ; P. Batude ; B. Mathieu ; E. Avelar ; A. Ayres De Sousa ; G. Cibrario ; O. Rozeau ; J. Lacord ; O. Billoint ; C. Fenouillet-Béranger ; S. Guissi ; D. Fried ; P. Morin ; J. P. Noel ; B. Giraud ; S. Thuries ; F. Arnaud ; M. Vinet</i>	
20.4 - POWER AWARE FINFET AND LATERAL NANOSHEET FET TARGETING FOR 3NM CMOS TECHNOLOGY	501
<i>D. Yakimets ; M. Garcia Bardon ; D. Jang ; P. Schuddinck ; Y. Sherazi ; P. Weckx ; K. Miyaguchi ; B. Parvais ; P. Raghavan ; A. Spessot ; D. Verkest ; A. Mocuta</i>	
20.5 - STACKED NANOSHEET FORK ARCHITECTURE FOR SRAM DESIGN AND DEVICE CO-OPTIMIZATION TOWARD 3NM	505
<i>P. Weckx ; J. Ryckaert ; V. Putcha ; A. De Keersgieter ; J. Boemmels ; P. Schuddinck ; D. Jang ; D. Yakimets ; M. G. Bardon ; L. -å. Ragnarsson ; P. Raghavan ; R. R. Kim ; A. Spessot ; D. Verkest ; A. Mocuta</i>	
20.6 - A NOVEL PERFORMANCE MODEL FOR STATE-OF-THE-ART PROCESSORS BY MODERNIZATION OF RENT'S RULE	509
<i>D. Prasad ; S. Sinha ; B. Cline ; S. Moore ; A. Naeemi</i>	
21.1 - IMPACT OF EXTERNAL MAGNETIC FIELD ON EMBEDDED PERPENDICULAR STT-MRAM TECHNOLOGY QUALIFIED FOR SOLDER REFLOW	513
<i>Chia-Yu Wang ; Meng-Chun Shih ; Yung-Huei Lee ; Wayne Wang ; Luc Thomas ; Yuan-Jen Lee ; Huanlong Liu ; Jian Zhu ; Guenole Jan ; Allen Wang ; Tom Zhong ; Po-Kang Wang ; Derek Lin ; Chia-Hsiang Chen ; Chih-Yang Chang ; Chih-Hui Weng ; Tien-Wei Chiang ; Kuei-Hung Shen ; William J. Gallagher ; Harry Chuang</i>	
21.2 - EXPERIMENTAL AND THEORETICAL VERIFICATION OF CHANNEL CONDUCTIVITY DEGRADATION DUE TO GRAIN BOUNDARIES AND DEFECTS IN 3D NAND	517
<i>A. Subirats ; A. Arreghini ; E. Capogreco ; R. Delhougne ; C. -L. Tan ; A. Hikavy ; L. Breuil ; R. Degraeve ; V. Putcha ; G. Van Den Bosch ; D. Linten ; A. Furnémont</i>	
21.3 - IMPACT OF TEMPERATURE ON THE AMPLITUDE OF RTN FLUCTUATIONS IN 3-D NAND FLASH CELLS	521
<i>G. Nicosia ; A. Mannara ; D. Resnati ; G. M. Paolucci ; P. Tessariol ; A. L. Lacaita ; A. S. Spinelli ; A. Goda ; C. Monzio Compagnoni</i>	
21.4 - RTN BASED OXYGEN VACANCY PROBING METHOD FOR OX-RRAM RELIABILITY CHARACTERIZATION AND ITS APPLICATION IN TAIL BITS	525
<i>P. Huang ; D. B. Zhu ; C. Liu ; Z. Zhou ; Z. Dong ; H. Jiang ; W. S. Shen ; L. F. Liu ; X. Y. Liu ; J. F. Kang</i>	
21.5 - FUNDAMENTAL LIMITATIONS OF EXISTING MODELS AND FUTURE SOLUTIONS FOR DIELECTRIC RELIABILITY AND RRAM APPLICATIONS (INVITED)	529
<i>E. Wu ; A. Kim ; T. Ando ; R. Muralidhar ; B. Li ; R. Southwick ; P. Jamison ; T. Shaw ; J. Stathis ; G. Bonilla</i>	
21.6 - OVERCOMING THE RELIABILITY LIMITATION IN THE ULTIMATELY SCALED DRAM USING SILICON MIGRATION TECHNIQUE BY HYDROGEN ANNEALING	533
<i>Seong-Wan Ryu ; Kyungkyu Min ; Jungho Shin ; Heimi Kwon ; Donghoon Nam ; Taekyung Oh ; Tae-Su Jang ; Minsoo Yoo ; Yongtaik Kim ; Sungjoo Hong</i>	
22.1 - HIGH-K METAL GATE FUNDAMENTAL LEARNING AND MULTI-VT OPTIONS FOR STACKED NANOSHEET GATE-ALL-AROUND TRANSISTOR	537
<i>Jingyun Zhang ; Takashi Ando ; Chun Wing Yeung ; Miaomiao Wang ; Ohseong Kwon ; Rohit Galatage ; Robin Chao ; Nicolas Loubet ; Bum Ki Moon ; Ruqiang Bao ; Reinaldo A. Vega ; Juntao Li ; Chen Zhang ; Zuoguang Liu ; Myunggil Kang ; Xin Miao ; Junli Wang ; Sivananda Kanakasabapathy ; Veeraraghavan S. Basker ; Hemanth Jagannathan ; Tenko Yamashita</i>	
22.2 - HIGHLY CONDUCTIVE METAL GATE FILL INTEGRATION SOLUTION FOR EXTREMELY SCALED RMG STACK FOR 5 NM & BEYOND	541
<i>N. Yoshida ; S. Hassan ; W. Tang ; Y. Yang ; W. Zhang ; S. C. Chen ; L. Dong ; H. Zhou ; M. Jin ; M. Okazaki ; J. Park ; N. Bekiaris ; R. Hung ; J. Zhou ; Y. Lei ; P. Ma ; X. Tang ; T. Miyashita ; N. Kim ; E. Yieh</i>	

22.3 - INTEGRATED DUAL SPE PROCESSES WITH LOW CONTACT RESISTIVITY FOR FUTURE CMOS TECHNOLOGIES	545
<i>Heng Wu ; Soon-Cheon Seo ; Chengyu Niu ; Wei Wang ; Gen Tsutsui ; Oleg Gluschenkov ; Zuoguang Liu ; Alexandru Petrescu ; Adra Carr ; Sam Choi ; Stan Tsai ; Chanro Park ; Indira Seshadri ; Anuja Desilva ; Abraham Arceo ; George Yang ; Muthumanickam Sankarapandian ; Chris Prindle ; Kerem Akarvardar ; Curtis Durfee ; Jie Yang ; Praneet Adusumilli ; Bruce Miao ; Jay Strane ; Walter Kleemeier ; Mark Raymond ; Kisik Choi ; Fee-Li Lie ; Tenko Yamashita ; Andreas Knorr ; Dinesh Gupta ; Dechao Guo ; Rama Divakaruni ; Huiming Bu ; Mukesh Khare</i>	
22.4 - COMPREHENSIVE STUDY OF GA ACTIVATION IN SI, SIGE AND GE WITH $5 \times 10^{-10} \Omega \cdot \text{CM}^2$ CONTACT RESISTIVITY ACHIEVED ON GA DOPED GE USING NANOSECOND LASER ACTIVATION	549
<i>Lin-Lin Wang ; Hao Yu ; M. Schaekers ; J. -L. Everaert ; A. Franquet ; B. Douhard ; L. Date ; J. Del Agua Borntiquel ; K. Hollar ; F. A. Khaja ; W. Aderhold ; A. J. Mayur ; J. Y. Lee ; H. Van Meer ; D. Mocuta ; N. Horiguchi ; N. Collaert ; K. De Meyer ; Yu-Long Jiang</i>	
22.5 - CLUSTER-PREFORMING-DEPOSITED AMORPHOUS WSI_N (N = 12) INSERTION FILM OF LOW SBH AND HIGH DIFFUSION BARRIER FOR DIRECT CU CONTACT	553
<i>Naoya Okada ; Noriyuki Uchida ; Sinichi Ogawa ; Kazuhiko Endo ; Toshihiko Kanayama</i>	
23.1 - NEGATIVE CAPACITANCE ENABLES FINFET AND FDSOI SCALING TO 2 NM NODE	557
<i>Vita Pi-Ho Hu ; Pin-Chieh Chiu ; Angada B. Sachid ; Chenming Hu</i>	
23.2 - ENERGY-EFFICIENT HFALO_x NCFET: USING GATE STRAIN AND DEFECT PASSIVATION TO REALIZE NEARLY HYSTERESIS-FREE SUB-25MV/DEC SWITCH WITH ULTRALOW LEAKAGE	561
<i>Chia-Chi Fan ; Chun-Hu Cheng ; Yi-Ru Chen ; Chien Liu ; Chun-Yen Chang</i>	
23.3 - FERROELECTRIC AL:HFO₂ NEGATIVE CAPACITANCE FETS	565
<i>M. H. Lee ; P. -G. Chen ; S. -T. Fan ; Y. -C. Chou ; C. -Y. Kuo ; C. -H. Tang ; H. -H. Chen ; S. -S. Gu ; R. -C. Hong ; Z. -Y. Wang ; S. -Y. Chen ; C. -Y. Liao ; K. -T. Chen ; S. T. Chang ; M. -H. Liao ; K. -S. Li ; C. W. Liu</i>	
23.4 - PHYSICS AND TECHNOLOGY OF ELECTRONIC INSULATOR-TO-METAL TRANSITION (E-IMT) FOR RECORD HIGH ON/OFF RATIO AND LOW VOLTAGE IN DEVICE APPLICATIONS	569
<i>Jianqiang Lin ; Khan Alam ; Leonidas Ocola ; Zhen Zhang ; Suman Datta ; Shriram Ramanathan ; Supratik Guha</i>	
23.5 - SUB-60 MV/DEC FERROELECTRIC HZO MOS₂ NEGATIVE CAPACITANCE FIELD-EFFECT TRANSISTOR WITH INTERNAL METAL GATE: THE ROLE OF PARASITIC CAPACITANCE	573
<i>M. Si ; C. Jiang ; C. -J. Su ; Y. -T. Tang ; L. Yang ; W. Chung ; M. A. Alam ; P. D. Ye</i>	
23.6 - NEGATIVE CAPACITANCE 2D MOS₂ TRANSISTORS WITH SUB-60MV/DEC SUBTHRESHOLD SWING OVER 6 ORDERS, 250 $\mu\text{A}/\mu\text{M}$ CURRENT DENSITY, AND NEARLY-HYSTERESIS-FREE	577
<i>Zhihao Yu ; Hanchen Wang ; Weisheng Li ; Sheng Xu ; Xiongfei Song ; Shuxian Wang ; Peng Wang ; Peng Zhou ; Yi Shi ; Yang Chai ; Xinran Wang</i>	
23.7 - NBO₂ BASED THRESHOLD SWITCH DEVICE WITH HIGH OPERATING TEMPERATURE (>85 C °) FOR STEEP-SLOPE MOSFET (~2MV/DEC) WITH ULTRA-LOW VOLTAGE OPERATION AND IMPROVED DELAY TIME	581
<i>Jaehyuk Park ; Dongwook Lee ; Jongmyung Yoo ; Hyunsang Hwang</i>	
24.1 - HYBRID III-V/SI DFB LASER INTEGRATION ON A 220 MM FULLY CMOS-COMPATIBLE SILICON PHOTONICS PLATFORM	585
<i>B. Szelag ; K. Hassan ; L. Adelmini ; E. Ghegin ; Ph. Rodriguez ; S. Bensalem ; F. Nemouchi ; T. Bria ; M. Brihoum ; P. Brianceau ; E. Vermande ; O. Pesenti ; A. Schembri ; R. Crochemore ; S. Dominguez ; M. C. Roure ; B. Montmayeul ; L. Sanchez ; C. Jany</i>	
24.2 - QUANTUM CONFINEMENT EFFECTS IN GESN/SIGESN HETEROSTRUCTURE LASERS	589
<i>D. Stange ; N. Von Den Driesch ; D. Rainko ; T. Zabel ; B. Marzban ; Z. Ikonic ; P. Zaumseil ; G. Capellini ; S. Manti ; J. Witzens ; H. Sigg ; D. Grützmacher ; D. Buca</i>	
24.3 - MONOLITHIC INTEGRATION OF O-BAND PHOTONIC TRANSCEIVERS IN A “ZERO-CHANGE” 32NM SOI CMOS	593
<i>S. Moazeni ; A. Atabaki ; D. Cheian ; S. Lin ; R. J. Ram ; V. Stojanovic</i>	
24.4 - TUNNEL-MODULATED GE LED/LASER LIGHT SOURCE AND A SUB-THERMAL VOLTAGE SWITCHING DETECTOR FOR THE MONOLITHIC ON-CHIP OPTICAL TRANSCEIVER	597
<i>R. Koerner ; I. A. Fischer ; R. Soref ; D. Schwarz ; C. J. Clausen ; L. Hänel ; M. Oehme ; J. Schulze</i>	
24.5 - A NOVEL 25 GBPS ELECTRO-OPTIC POKELS MODULATOR INTEGRATED ON AN ADVANCED SI PHOTONIC PLATFORM	601
<i>F. Eltes ; M. Kroh ; D. Caimi ; C. Mai ; Y. Popoff ; G. Winzer ; D. Petousi ; S. Lischke ; J. E. Ortmann ; L. Czornomaz ; L. Zimmermann ; J. Fompeyrine ; S. Abel</i>	

25.1 - FAST SWITCHING PERFORMANCE BY 20 A / 730 V ALGAN/GAN MIS-HFET USING ALON GATE INSULATOR.....	605
<i>S. Nakazawa ; H. -A. Shih ; N. Tsurumi ; Y. Anda ; T. Hatsuda ; T. Ueda ; M. Nozaki ; T. Yamada ; T. Hosoi ; T. Shimura ; H. Watanabe ; T. Hashizume</i>	
25.2 - AN INTERDIGITATED GAN MIS-HEMT/SBD NORMALLY-OFF POWER SWITCHING DEVICE WITH LOW ON-RESISTANCE AND LOW REVERSE CONDUCTION LOSS.....	609
<i>Jiacheng Lei ; Jin Wei ; Gaofei Tang ; Qingkai Qian ; Mengyuan Hua ; Zhaofu Zhang ; Zheyang Zheng ; Kevin J. Chen</i>	
25.3 - LARGE SIGNAL LINEARITY ENHANCEMENT OF ALGAN/GAN HIGH ELECTRON MOBILITY TRANSISTORS BY DEVICE-LEVEL VT ENGINEERING FOR TRANSCONDUCTANCE COMPENSATION.....	613
<i>Sameer Joglekar ; Ujwal Radhakrishna ; Daniel Piedra ; Dimitri Antoniadis ; Tomás Palacios</i>	
25.4 - 200V, 4MV/CM LATERAL DIAMOND MOSFET.....	617
<i>T. T. Pham ; J. Pernot ; C. Masante ; D. Eon ; E. Gheeraert ; G. Chicot ; F. Udrea ; N. Rouger</i>	
25.5 - NOVEL 5V-EDMOS TRANSISTOR WITH A RECORD /MAX OF 450 GHZ IN A BASELINE 40NM CMOS TECHNOLOGY.....	621
<i>Thanh Viet Dinh ; Jan Sonsky ; Jan Claes ; Oliver Dieball ; Guido T. Sasse ; Celine Detcheverry</i>	
25.6 - HIGH REJECTION UNII 5.2GHZ WIDEBAND BULK ACOUSTIC WAVE FILTERS USING UNDOPED SINGLE CRYSTAL ALN-ON-SIC RESONATORS.....	625
<i>Michael D. Hodge ; Ramakrishna Vetury ; Shawn R. Gibb ; Mary Winters ; Pinal Patel ; Michael A. McLain ; Ya Shen ; Dae Ho Kim ; Joe Jech ; Ken Fallon ; Rohan Houlden ; David M. Aichele ; Jeffrey B. Shealy</i>	
26.1 - TRANSPARENT ARTIFACT-FREE GRAPHENE ELECTRODES FOR COMPACT CLOSED-LOOP OPTOGENETICS SYSTEMS.....	629
<i>Xin Liu ; Yichen Lu ; Ege Iseri ; Chi Ren ; Haixin Liu ; Takaki Komiyama ; Duygu Kuzum</i>	
26.2 - HIGH-YIELD PASSIVE SI PHOTODIODE ARRAY TOWARDS OPTICAL NEURAL RECORDING.....	633
<i>D. Mao ; J. Morley ; Z. Zhang ; M. Donnelly ; G. Xu</i>	
26.3 - INTERACTIONS OF NANOWIRES WITH CELLS AND TISSUE.....	637
<i>Christelle N. Prinz</i>	
26.4 - INTEGRATION OF FINFETS AND 3D NANOPROBES DEVICES ON A COMMON BIO-PLATFORM FOR MONITORING ELECTRICAL ACTIVITY OF SINGLE NEURONS.....	641
<i>A. Casanova ; M. -C. Blatche ; F. Mathieu ; L. Bettamin ; H. Martin ; D. Gonzalez-Dunia ; L. Nicu ; G. Larrieu</i>	
26.5 - DIRECT CHARACTERIZATION OF CIRCULATING DNA IN BLOOD PLASMA USING μLAS TECHNOLOGY.....	645
<i>R. Malbec ; B. Chami ; H. H. T. Ngo ; A. Didelot ; F. Garlan ; S. Garrigou ; V. Taly ; Lorène Aeschbach ; Evgeniya Trofimenko ; Vincent Dion ; A. Boutonnet-Rodat ; F. Ginot ; A. Bancaud</i>	
26.6 - NANOPORES INCORPORATING ITO ELECTRODES FOR ELECTRICAL GATING OF DNA AT DIFFERENT FOLDING STATES.....	649
<i>Xin Zhu ; Xiaowei Wang ; Zhen Cao ; Zhi Ye ; Chaoming Gu ; Chuan Hong Jin ; Yang Liu</i>	
28.1 - MODELING-BASED DESIGN OF BRAIN-INSPIRED SPIKING NEURAL NETWORKS WITH RRAM LEARNING SYNAPSES.....	653
<i>G. Pedretti ; S. Bianchi ; V. Milo ; A. Calderoni ; N. Ramaswamy ; D. Ielmini</i>	
28.2 - A 16MB DUAL-MODE RERAM MACRO WITH SUB-14NS COMPUTING-IN-MEMORY AND MEMORY FUNCTIONS ENABLED BY SELF-WRITE TERMINATION SCHEME.....	657
<i>Wei-Hao Chen ; Wen-Jang Lin ; Li-Ya Lai ; Shuangchen Li ; Chien-Hua Hsu ; Huan-Ting Lin ; Heng-Yuan Lee ; Jian-Wei Su ; Yuan Xie ; Shyh-Shyuan Sheu ; Meng-Fan Chang</i>	
28.3 - COMPRESSED SENSING RECOVERY USING COMPUTATIONAL MEMORY.....	661
<i>M. Le Gallo ; A. Sebastian ; G. Cherubini ; H. Giefers ; E. Eleftheriou</i>	
28.4 - DATA-AWARE NAND FLASH MEMORY FOR INTELLIGENT COMPUTING WITH DEEP NEURAL NETWORK.....	665
<i>Ken Takeuchi</i>	
28.5 - RECONFIGURABLE NAND/NOR LOGIC GATES IN 28 NM HKMG AND 22 NM FD-SOI FEFET TECHNOLOGY.....	669
<i>E. T. Breyer ; H. Mulaosmanovic ; T. Mikolajick ; S. Slesazek</i>	
29.1 - A 10NM HIGH PERFORMANCE AND LOW-POWER CMOS TECHNOLOGY FEATURING 3RD GENERATION FINFET TRANSISTORS, SELF-ALIGNED QUAD PATTERNING, CONTACT OVER ACTIVE GATE AND COBALT LOCAL INTERCONNECTS.....	673
<i>C. Auth ; A. Aliyarukunju ; M. Asoro ; D. Bergstrom ; V. Bhagwat ; J. Birdsall ; N. Bisnik ; M. Buehler ; V. Chikarmane ; G. Ding ; Q. Fu ; H. Gomez ; W. Han ; D. Hanken ; M. Haran ; M. Hattendorf ; R. Heussner ; H. Hiramatsu ; B. Ho ; S. Jaloviar ; I. Jin ; S. Joshi ; S. Kirby ; S. Kosaraju ; H. Kothari ; G. Leatherman ; K. Lee ; J. Leib ; A. Madhavan ; K. Marla ; H. Meyer ; T. Mule ; C. Parker ; S. Parthasarathy ; C. Peltó ; L. Pipes ; I. Post ; M. Prince ; A. Rahman ; S. Rajamani ; A. Saha ; J. Dacuna Santos ; M. Sharma ; V. Sharma ; J. Shin ; P. Sinha ; P. Smith ; M. Sprinkle ; A. St. Amour ; C. Staus ; R. Suri ; D. Towner ; A. Tripathi ; A. Tura ; C. Ward ; A. Yeoh</i>	

29.2 - PERFORMANCE AND DESIGN CONSIDERATIONS FOR GATE-ALL-AROUND STACKED-NANOWIRES FETS	677
<i>S. Barraud ; V. Lapras ; B. Previtali ; M. P. Samson ; J. Lacord ; S. Martinie ; M. -A. Jaud ; S. Athanasiou ; F. Triozon ; O. Rozeau ; J. M. Hartmann ; C. Vizioz ; C. Comboroure ; F. Andrieu ; J. C. Barbé ; M. Vinet ; T. Ernst</i>	
29.3 - ACCURATE PERFORMANCE EVALUATION FOR THE HORIZONTAL NANOSHEET STANDARD-CELL DESIGN SPACE BEYOND 7NM TECHNOLOGY	681
<i>Y. M. Lee ; M. H. Na ; A. Chu ; A. Young ; T. Hook ; L. Liebmann ; E. J. Nowak ; S. H. Baek ; R. Sengupta ; H. Trombley ; X. Miao</i>	
29.4 - 22FFL: A HIGH PERFORMANCE AND ULTRA LOW POWER FINFET TECHNOLOGY FOR MOBILE AND RF APPLICATIONS	685
<i>B. Sell ; B. Bigwood ; S. Cha ; Z. Chen ; P. Dhage ; P. Fan ; M. Giraud-Carrier ; A. Kar ; E. Karl ; C. -J. Ku ; R. Kumar ; T. Lajoie ; H. -J. Lee ; G. Liu ; S. Liu ; Y. Ma ; S. Mudanai ; L. Nguyen ; L. Paulson ; K. Phoa ; K. Pierce ; A. Roy ; R. Russell ; J. Sandford ; J. Stoeger ; N. Stojanovic ; A. Sultana ; J. Waldemer ; J. Wan ; W. Xu ; D. Young ; J. Zhang ; Y. Zhang ; P. Bai</i>	
29.5 - A 7NM CMOS TECHNOLOGY PLATFORM FOR MOBILE AND HIGH PERFORMANCE COMPUTE APPLICATION	689
<i>S. Narasimha ; B. Jagannathan ; A. Ogino ; D. Jaeger ; B. Greene ; C. Sheraw ; K. Zhao ; B. Haran ; U. Kwon ; A. K. M. Mahalingam ; B. Kannan ; B. Morganfeld ; J. Dechene ; C. Radens ; A. Tessier ; A. Hassan ; H. Narisetty ; I. Ahsan ; M. Aminpur ; C. An ; M. Aquilino ; A. Arya ; R. Augur ; N. Baliga ; R. Bhelkar ; G. Biery ; A. Blauberg ; N. Borjemscaia ; A. Bryant ; L. Cao ; V. Chauhan ; M. Chen ; L. Cheng ; J. Choo ; C. Christiansen ; T. Chu ; B. Cohen ; R. Coleman ; D. Conklin ; S. Crown ; A. da Silva ; D. Dechene ; G. Derderian ; S. Deshpande ; G. Dillway ; K. Donegan ; M. Eller ; Y. Fan ; Q. Fang ; A. Gassaria ; R. Gauthier ; S. Ghosh ; G. Gifford ; T. Gordon ; M. Gribelyuk ; G. Han ; J. H. Han ; K. Han ; M. Hasan ; J. Higman ; J. Holt ; L. Hu ; L. Huang ; C. Huang ; T. Hung ; Y. Jin ; J. Johnson ; S. Johnson ; V. Joshi ; M. Joshi ; P. Justison ; S. Kalaga ; T. Kim ; W. Kim ; R. Krishnan ; B. Krishnan ; K. Anil ; M. Kumar ; J. Lee ; R. Lee ; J. Lemon ; S. L. Liew ; P. Lindo ; M. Lingalugari ; M. Lipinski ; P. Liu ; J. Liu ; S. Lucarini ; W. Ma ; E. Maciejewski ; S. Madisetti ; A. Malinowski ; J. Mehta ; C. Meng ; S. Mitra ; C. Montgomery ; H. Nayfeh ; T. Nigam ; G. Northrop ; K. Onishi ; C. Ordonio ; M. Ozbek ; R. Pal ; S. Parihar ; O. Patterson ; E. Ramanathan ; I. Ramirez ; R. Ranjan ; J. Sarad ; V. Sardesai ; S. Saudari ; C. Schiller ; B. Senapati ; C. Serrau ; N. Shah ; T. Shen ; H. Sheng ; J. Shepard ; Y. Shi ; M. C. Silvestre ; D. Singh ; Z. Song ; J. Sporre ; P. Srinivasan ; Z. Sun ; A. Sutton ; R. Sweeney ; K. Tabakman ; M. Tan ; X. Wang ; E. Woodard ; G. Xu ; D. Xu ; T. Xuan ; Y. Yan ; J. Yang ; K. B. Yeap ; M. Yu ; A. Zainuddin ; J. Zeng ; K. Zhang ; M. Zhao ; Y. Zhong ; R. Carter ; C. -H. Lin ; S. Grunow ; C. Child ; M. Lagus ; R. Fox ; E. Kaste ; G. Gomba ; S. Samavedam ; P. Agnello ; D. K. Sohn</i>	
30.1 - DEVELOPMENT OF SUSTAINABLE SMART SOCIETY BASED ON TRANSFORMATIVE ELECTRONICS	693
<i>M. Ogura ; Y. Ando ; S. Usami ; K. Nagamatsu ; M. Kushimoto ; M. Deki ; A. Tanaka ; S. Nitta ; Y. Honda ; M. Pristovsek ; H. Kawai ; S. Yagi ; H. Amano</i>	
31.1 - TIME-RESOLVED QUANTUM TRANSPORT FOR OPTOELECTRONICS	697
<i>F. Michelini ; K. Beltako ; M. Bescond ; N. Cavassilas ; L. Raymond</i>	
31.2 - COMPUTATIONAL STUDY OF GATE-INDUCED DRAIN LEAKAGE IN 2D-SEMICONDUCTOR FIELD-EFFECT TRANSISTORS	701
<i>Jiahao Kang ; Wei Cao ; Arnab Pal ; Sumeet Pandey ; Steve Kramer ; Richard Hill ; Gurtej Sandhu ; Kaustav Banerjee</i>	
31.3 - HOW TO DERIVE THE HIGHEST MOBILITY FROM 2D FETS — A FIRST-PRINCIPLE STUDY	705
<i>Arnab Pal ; Wei Cao ; Jiahao Kang ; Kaustav Banerjee</i>	
31.4 - A UNIFIED SURFACE POTENTIAL BASED PHYSICAL COMPACT MODEL FOR BOTH UNIPOLAR AND AMBIPOLAR 2D-FET: EXPERIMENTAL VERIFICATION AND CIRCUIT DEMONSTRATION	709
<i>Lingfei Wang ; Yang Li ; Xuwei Feng ; Kah-Wee Ang ; Xiao Gong ; Aaron Thean ; Gengchiao Liang</i>	
31.5 - QUANTITATIVE MODEL FOR SWITCHING ASYMMETRY IN PERPENDICULAR MTJ: A MATERIAL-DEVICE-CIRCUIT CO-DESIGN	713
<i>Deepanjan Datta ; Hemant Dixit ; Samarth Agarwal ; Avirup Dasgupta ; Michael Tran ; Dimitri Houssameddine ; Yogesh Singh Chauhan ; Danny Shum ; Francis Benistant</i>	
32.1 - THE IMPACT OF SEQUENTIAL-3D INTEGRATION ON SEMICONDUCTOR SCALING ROADMAP	717
<i>A. Mallik ; A. Vandooren ; L. Witters ; A. Walke ; J. Franco ; Y. Sherazi ; P. Weckx ; D. Yakimets ; M. Bardon ; B. Parvais ; P. Debacker ; B. W. Ku ; S. K. Lim ; A. Mocuta ; D. Mocuta ; J. Ryckaert ; N. Collaert ; P. Raghavan</i>	
32.2 - HIGH PERFORMANCE LOW TEMPERATURE FINFET WITH DSPER, GATE LAST AND SELF ALIGNED CONTACT FOR 3D SEQUENTIAL INTEGRATION	721
<i>J. Micout ; V. Lapras ; P. Batude ; C. Fenouillet-Beranger ; J. Lacord ; B. Sklenard ; B. Mathieu ; Q. Rafhay ; V. Mazzocchi ; J. -P. Colinge ; L. Lachal ; X. Garros ; M. Casse ; A. Toffoli ; G. Romano ; F. Allain ; L. Brunet ; J. -M. Hartmann ; R. Bortolin ; F. Mazen ; S. Barraud ; N. Rambal ; C. Tabone ; M. -P. Samson ; P. Besombes ; V. Delaye ; Z. Saghi ; V. Loup ; C. Comboroure ; V. Balan ; L. Desvoivres ; C. Vizioz ; G. Ghibaudo ; M. Vinet</i>	

32.3 - MATERIAL INNOVATION FOR MOL, BEOL, AND 3D INTEGRATION	725
<i>J. Koike ; M. Hosseini ; H. T. Hai ; D. Ando ; Y. Sutou</i>	
32.4 - SCALABLE, SUB 2μM PITCH, CU/SICN TO CU/SICN HYBRID WAFER-TO-WAFER BONDING TECHNOLOGY	729
<i>Eric Beyne ; Soon-Wook Kim ; Lan Peng ; Nancy Heylen ; Joke De Messemaeker ; Oguzhan Orkut Okudur ; Alain Phommahaxay ; Tae-Gon Kim ; Michele Stucchi ; Dimitrios Velenis ; Andy Miller ; Gerald Beyer</i>	
32.5 - HIGH EFFICIENCY DIRECT LIQUID JET IMPINGEMENT COOLING OF HIGH POWER DEVICES USING A 3D-SHAPED POLYMER COOLER	733
<i>T. Tiwei ; H. Oprins ; V. Cherman ; G. Van Der Plas ; I. De Wolf ; E. Beyne ; M. Baelmans</i>	
33.1 - SMART GAN PLATFORM: PERFORMANCE & CHALLENGES	737
<i>Chun-Lin Tsai ; Yun-Hsiang Wang ; M. -H. Kwan ; P. -C. Chen ; F. -W. Yao ; S. -C. Liu ; J. -L. Yu ; C. -L. Yeh ; R. -Y. Su ; W. Wang ; W. -C. Yang ; K. -Y. Wong ; Y. -S. Lin ; M. -C. Lin ; H. -Y. Wu ; C. -M. Chen ; C. -Y. Yu ; C. -B. Wu ; M. -H. Chang ; J. -S. You ; T. -M. Huang ; S. -P. Wang ; L. Y. Tsai ; Chan-Hong Chern ; H. C. Tuan ; Alex Kalnitsky</i>	
33.2 - REVERSE-BIAS STABILITY AND RELIABILITY OF HOLE-BARRIER-FREE E-MODE LPCVD-SiNX/GAN MIS-FETS	741
<i>Mengyuan Hua ; Jin Wei ; Qilong Bao ; Jiabei He ; Zhaofu Zhang ; Zheyang Zheng ; Jiacheng Lei ; Kevin J. Chen</i>	
33.3 - IMPROVEMENT OF POSITIVE BIAS TEMPERATURE INSTABILITY CHARACTERISTIC IN GAN MOSFETS BY CONTROL OF IMPURITY DENSITY IN SiO₂ GATE DIELECTRIC	745
<i>T. Yonehara ; Y. Kajiwara ; D. Kato ; K. Uesugi ; T. Shimizu ; Y. Nishida ; H. Ono ; A. Shindome ; A. Mukai ; A. Yoshioka ; M. Kuraguchi</i>	
33.4 - EVIDENCE OF DEFECT BAND IN CARBON-DOPED GAN CONTROLLING LEAKAGE CURRENT AND TRAPPING DYNAMICS	749
<i>C. Koller ; G. Pobegen ; C. Ostermaier ; D. Pogany</i>	
33.5 - TOTAL SUPPRESSION OF DYNAMIC-RON IN ALGAN/GAN-HEMTS THROUGH PROTON IRRADIATION	753
<i>M. Meneghini ; A. Tajalli ; P. Moens ; A. Banerjee ; A. Stockman ; M. Tack ; S. Gerardin ; M. Bagatin ; A. Paccagnella ; E. Zanoni ; G. Meneghesso</i>	
34.1 - ADVANCED SILICON PHOTONICS TECHNOLOGY PLATFORM LEVERAGING A SEMICONDUCTOR SUPPLY CHAIN	757
<i>P. De Dobbelaere ; A. Dahl ; A. Mekis ; B. Chase ; B. Weber ; B. Welch ; D. Foltz ; G. Armijo ; G. Masini ; G. McGee ; G. Wong ; J. Balardeta ; J. Dotson ; J. Schramm ; K. Hon ; K. Khaiv ; K. Robertson ; K. Stechschulte ; K. Yokoyama ; L. Planchon ; L. Tullgren ; M. Eker ; M. Mack ; M. Peterson ; N. Rudnick ; P. Milton ; P. Sun ; R. Bruck ; R. Zhou ; S. Denton ; S. Fath-Pour ; S. Gloeckner ; S. Jackson ; S. Pang ; S. Sahni ; S. Wang ; S. Yu ; T. Pinguet ; Y. De Koninck ; Y. Chi ; Y. Liang</i>	
34.2 - RELIABLE 50GB/S SILICON PHOTONICS PLATFORM FOR NEXT-GENERATION DATA CENTER OPTICAL INTERCONNECTS	761
<i>P. Absil ; K. Croes ; A. Lesniewska ; P. De Heyn ; Y. Ban ; B. Snyder ; J. De Coster ; F. Fodor ; V. Simons ; S. Balakrishnan ; G. Lepage ; N. Golshani ; S. Lardenois ; S. A. Srinivasan ; H. Chen ; W. Vanherle ; R. Loo ; R. Boufadil ; M. Detalle ; A. Miller ; P. Verheyen ; M. Pantouvaki ; J. Van Campenhout</i>	
34.3 - DEVELOPMENTS IN 300MM SILICON PHOTONICS USING TRADITIONAL CMOS FABRICATION METHODS AND MATERIALS	765
<i>C. Baudot ; M. Douix ; S. Guerber ; S. Cr�mer ; N. Vulliet ; J. Planchot ; R. Blanc ; L. Babaud ; C. Alonso-Ramos ; D. Benedikovich ; D. P�rez-Galacho ; S. Messaoud�ne ; S. Kerdiles ; P. Acosta-Alba ; C. Euvrard-Colnat ; E. Cassan ; D. Marris-Morini ; L. Vivien ; F. Boeuf</i>	
34.4 - ADVANCED DEVICES AND PACKAGING OF SI-PHOTONICS-BASED OPTICAL TRANSCEIVER FOR OPTICAL INTERCONNECTION	769
<i>K. Kurata ; K. Yashiki ; J. Fujikata ; T. Horikawa ; K. Kinoshita ; J. Ushida ; M. Tokushima ; Y. Suzuki ; D. Okamoto ; S. Takahashi ; A. Ukita ; K. Takemura ; Y. Ibusuki ; T. Shimizu ; M. Kurihara ; Y. Hagihara ; T. Mogami ; T. Nakamura</i>	
34.5 - FEMTO-JOULE-PER-BIT INTEGRATED NANOPHOTONICS AND CHALLENGE FOR OPTICAL COMPUTATION	773
<i>Masaya Notomi ; Kengo Nozaki ; Akihiko Shinya ; Masato Takiguchi</i>	
35.1 - NEGF BASED TRANSPORT MODELLING WITH A FULL-BAND, PSEUDOPOTENTIAL HAMILTONIAN: THEORY, IMPLEMENTATION AND FULL DEVICE SIMULATIONS	776
<i>Marco G. Pala ; Oves Badami ; David Esseni</i>	
35.2 - FIRST-PRINCIPLES BASED QUANTUM TRANSPORT SIMULATIONS OF NANOSCALE FIELD EFFECT TRANSISTORS	780
<i>Mincheol Shin ; Hyo-Eun Jung ; Sungwoo Jung</i>	
35.3 - DOPANT DIFFUSION IN SI, SiGe AND Ge : TCAD MODEL PARAMETERS DETERMINED WITH DENSITY FUNCTIONAL THEORY	784
<i>Y. Park ; C. Zechner ; Y. Oh ; H. Kim ; I. Martin-Bragado ; E. M. Bazizi ; F. Benistant</i>	

35.4 - FIRST TOPOGRAPHY SIMULATION OF SIC-CHEMICAL-VAPOR-DEPOSITION TRENCH FILLING, DEMONSTRATING THE ESSENTIAL IMPACT OF THE GIBBS-THOMSON EFFECT	788
<i>K. Mochizuki ; S. Ji ; R. Kosugi ; Y. Yonezawa ; H. Okumura</i>	
35.5 - A PHYSICS-BASED INVESTIGATION OF PT-SALT DOPED CARBON NANOTUBES FOR LOCAL INTERCONNECTS	792
<i>J. Liang ; R. Ramos ; J. Dijon ; H. Okuno ; D. Kalita ; D. Renaud ; J. Lee ; V. P. Georgiev ; S. Berrada ; T. Sadi ; A. Asenov ; B. Uhlig ; K. Lilienthal ; A. Dhavamani ; F. Könemann ; B. Gotsmann ; G. Goncalves ; B. Chen ; K. Teo ; R. R. Pandey ; A. Todri-Saniai</i>	
36.1 - MOS₂/VO₂ VDW HETEROJUNCTION DEVICES: TUNABLE RECTIFIERS, PHOTODIODES AND FIELD EFFECT TRANSISTORS	796
<i>N. Oliva ; E. A. Casu ; C. Yan ; A. Krammer ; A. Magrez ; A. Schueler ; O. J. F. Martin ; A. M. Ionescu</i>	
36.2 - A SINGLE MAGNETIC-TUNNEL-JUNCTION STOCHASTIC COMPUTING UNIT	800
<i>Yang Lv ; Jian-Ping Wang</i>	
36.3 - NEUROMORPHIC COMPUTING THROUGH TIME-MULTIPLEXING WITH A SPIN-TORQUE NANO-OSCILLATOR	804
<i>M. Riou ; F. Abreu Araujo ; J. Torrejon ; S. Tsunegi ; G. Khalsa ; D. Querlioz ; P. Bortolotti ; V. Cros ; K. Yakushiji ; A. Fukushima ; H. Kubota ; S. Yuasa ; M. D. Stiles ; J. Grollier</i>	
36.4 - STDP SYNAPSE WITH OUTSTANDING STABILITY BASED ON A NOVEL INSULATOR-TO-METAL TRANSITION FET	808
<i>P. Stolar ; A. Schulman ; A. Kitoh ; A. Sawa ; I. H. Inoue</i>	
36.5 - ALL-ELECTRICAL UNIVERSAL CONTROL OF A DOUBLE QUANTUM DOT QUBIT IN SILICON MOS	812
<i>Patrick Harvey-Collard ; Ryan M. Jock ; N. Tobias Jacobson ; Andrew D. Baczewski ; Andrew M. Mounce ; Matthew J. Curry ; Daniel R. Ward ; John M. Anderson ; Ronald P. Manginell ; Joel R. Wendt ; Martin Rudolph ; Tammy Plum ; Michael P. Lilly ; Michel Pioro-Ladrière ; Malcolm S. Carroll</i>	
37.1 - SUB-NM EOT FERROELECTRIC HFO₂ ON P⁺GE WITH HIGHLY RELIABLE FIELD CYCLING PROPERTIES	816
<i>X. Tian ; L. Xu ; S. Shibayama ; T. Nishimura ; T. Yajima ; S. Migita ; A. Toriumi</i>	
37.2 - A COMPARATIVE STUDY OF STRAIN AND GE CONTENT IN SI_{1-x}GE_x CHANNEL USING PLANAR FETS, FINFETS, AND STRAINED RELAXED BUFFER LAYER FINFETS	820
<i>C. H. Lee ; S. Mochizuki ; R. G. Southwick ; J. Li ; X. Miao ; R. Bao ; T. Ando ; R. Galatage ; S. Siddiqui ; C. Labelle ; A. Knorr ; J. H. Stathis ; D. Guo ; V. Narayanan ; B. Haran ; H. Jagannathan</i>	
37.3 - HIGH PERFORMANCE AND RELIABLE STRAINED SIGE PMOS FINFETS ENABLED BY ADVANCED GATE STACK ENGINEERING	824
<i>Pouya Hashemi ; Takashi Ando ; Eduard A. Cartier ; Kam-Leung Lee ; John Bruley ; Choong-Hyun Lee ; Vijay Narayanan</i>	
37.4 - VERTICALLY STACKED GATE-ALL-AROUND SI NANOWIRE TRANSISTORS: KEY PROCESS OPTIMIZATIONS AND RING OSCILLATOR DEMONSTRATION	828
<i>H. Mertens ; R. Ritzenhaler ; V. Pena ; G. Santoro ; K. Kenis ; A. Schulze ; E. D. Litta ; S. A. Chew ; K. Devriendt ; R. Chiarella ; S. Demuyne ; D. Yakimets ; D. Jang ; A. Spessot ; G. Eneman ; A. Dangol ; P. Lagrain ; H. Bender ; S. Sun ; M. Korolik ; D. Kioussis ; M. Kim ; K. H. Bu ; S. C. Chen ; M. Cogorno ; J. Devrajan ; J. Machillot ; N. Yoshida ; N. Kim ; K. Barla ; D. Mocuta ; N. Horiguchi</i>	
37.5 - FIRST VERTICALLY STACKED GESN NANOWIRE PGA FETS WITH I_{ON} = 1850 μA/μM (VOV = VDS = -1V) ON SI BY GESN/GE CVD EPITAXIAL GROWTH AND OPTIMUM SELECTIVE ETCHING	832
<i>Yu-Shiang Huang ; Fang-Liang Lu ; Ya-Jui Tsou ; Chung-En Tsai ; Chung-Yi Lin ; Chih-Hao Huang ; C. W. Liu</i>	
38.1 - THRESHOLD SWITCHING SELECTOR AND ISIR INTEGRATION DEVELOPMENT FOR 3D CROSS-POINT STT-MRAM	836
<i>Hongxin Yang ; Xiaojie Hao ; Zihui Wang ; Roger Malmhall ; Huadong Gan ; Kimihiro Satoh ; Jing Zhang ; Dong Ha Jung ; Xiaobin Wang ; Yuchen Zhou ; Bing K. Yen ; Yiming Huai</i>	
38.2 - MRAM: ENABLING A SUSTAINABLE DEVICE FOR PERVASIVE SYSTEM ARCHITECTURES AND APPLICATIONS	840
<i>S. H. Kang ; C. Park</i>	
38.3 - KEY PARAMETERS AFFECTING STT-MRAM SWITCHING EFFICIENCY AND IMPROVED DEVICE PERFORMANCE OF 400° C-COMPATIBLE P-MTJS	844
<i>G. Hu ; M. G. Gottwald ; Q. He ; J. H. Park ; G. Lauer ; J. J. Nowak ; S. L. Brown ; B. Doris ; D. Edelstein ; E. R. Evarts ; P. Hashemi ; B. Khan ; Y. H. Kim ; C. Kothandaraman ; N. Marchack ; E. J. O'Sullivan ; M. Reuter ; R. P. Robertazzi ; J. Z. Sun ; T. Suwannisiri ; P. L. Trouilloud ; Y. Zhu ; D. C. Worledge</i>	
38.4 - PROBING MAGNETIC PROPERTIES OF STT-MRAM DEVICES DOWN TO SUB-20 NM USING SPIN-TORQUE FMR	848
<i>Luc Thomas ; Guenole Jan ; Son Le ; Santiago Serrano-Guisan ; Yuan-Jen Lee ; Huanlong Liu ; Jian Zhu ; Jodi Iwata-Harms ; Ru-Ying Tong ; Sahil Patel ; Vignesh Sundar ; Dongna Shen ; Yi Yang ; Renren He ; Jesmin Haq ; Zhongjian Teng ; Vinh Lam ; Paul Liu ; Yu-Jen Wang ; Tom Zhong ; Po-Kang Wang</i>	

38.5 - NOVEL APPROACH FOR NANO-PATTERNING MAGNETIC TUNNEL JUNCTIONS STACKS AT NARROW PITCH: A ROUTE TOWARDS HIGH DENSITY STT-MRAM APPLICATIONS	852
<i>V. D. Nguyen ; P. Sabon ; J. Chatterjee ; L. Tille ; P. Veloso Coelho ; S. Auffret ; R. Sousa ; L. Prejbeanu ; E. Gautier ; L. Vila ; B. Dieny</i>	
38.6 - SOLVING THE BEOL COMPATIBILITY CHALLENGE OF TOP-PINNED MAGNETIC TUNNEL JUNCTION STACKS	856
<i>J. Swerts ; E. Liu ; S. Couet ; S. Mertens ; S. Rao ; W. Kim ; K. Garello ; L. Souriau ; S. Kundu ; D. Crotti ; F. Yasin ; N. Jossart ; S. Sakhare ; T. Devolder ; S. Van Beek ; B. O'Sullivan ; S. Van Elshocht ; A. Furnemont ; G. S. Kar</i>	
39.1 - NON-FILAMENTARY (VMCO) MEMORY: A TWO-AND THREE-DIMENSIONAL STUDY ON SWITCHING AND FAILURE MODES	860
<i>U. Celano ; C. Gastaldi ; S. Subhechha ; B. Govoreanu ; G. Donadio ; A. Franquet ; T. Ahmad ; C. Detavernier ; O. Richard ; H. Bender ; L. Goux ; G. S. Kar ; P. Van Der Heide ; W. Vandervorst</i>	
39.2 - ULTRA FAST (<1 NS) ELECTRICAL CHARACTERIZATION OF SELF-HEATING EFFECT AND ITS IMPACT ON HOT CARRIER INJECTION IN 14NM FINFETS	864
<i>Yiming Qu ; Xi Lin ; Junkang Li ; Ran Cheng ; Xiao Yu ; Zejie Zheng ; Jiwu Lu ; Bing Chen ; Yi Zhao</i>	
39.3 - AN ULTRA-DENSE IRRADIATION TEST STRUCTURE WITH A NAND/NOR READOUT CHAIN FOR CHARACTERIZING SOFT ERROR RATES OF 14NM COMBINATIONAL LOGIC CIRCUITS	868
<i>Saurabh Kumar ; Minki Cho ; Luke Everson ; Hoonki Kim ; Qianying Tang ; Paul Mazanec ; Pascal Meinerzhagen ; Andres Malavasi ; Dan Lake ; Carlos Tokunaga ; Muhammad Khellah ; James Tschanz ; Shekhar Borkar ; Vivek De ; Chris H. Kim</i>	
39.4 - INVESTIGATION OF STATISTICAL RETENTION OF FILAMENTARY ANALOG RRAM FOR NEUROMORPHIC COMPUTING	872
<i>Meiran Zhao ; Huaqiang Wu ; Bin Gao ; Qingtian Zhang ; Wei Wu ; Shan Wang ; Yue Xi ; Dong Wu ; Ning Deng ; Shimeng Yu ; Hong-Yu Chen ; He Qian</i>	
39.5 - COMBATTING IC COUNTERFEITING USING SECURE CHIP ODOMETERS	876
<i>N. E. C. Akkaya ; B. Erbagci ; K. Mai</i>	
40.1 - HIGH-Q SILICON FIN BULK ACOUSTIC RESONATORS FOR SIGNAL PROCESSING BEYOND THE UHF	880
<i>M. Ramezani ; M. Ghatge ; R. Tabrizian</i>	
40.2 - MONOLITHICALLY 3D-PRINTED PRESSURE SENSORS FOR APPLICATION IN ELECTRONIC SKIN AND HEALTHCARE MONITORING	884
<i>Jinsu Yoon ; Bongsik Choi ; Yongwoo Lee ; Jungmin Han ; Jieun Lee ; Jinhee Park ; Yeamin Kim ; Dong Myong Kim ; Dae Hwan Kim ; Min-Ho Kang ; Sungho Kim ; Sung-Jin Choi</i>	
40.3 - A NOVEL TRIBOELECTRIC NANOGENERATOR WITH HIGH PERFORMANCE AND LONG DURATION TIME OF SINUSOIDAL CURRENT GENERATION	888
<i>Weon-Guk Kim ; Daewon Kim ; Seung-Bae Jeon ; Sang-Jae Park ; Il-Woong Tcho ; Hagvoul Bae ; Hwon Im ; Yang-Kyu Choi</i>	
40.4 - MEMS HETEROGENEOUS PACKAGED BROADBAND ELECTROMAGNETIC INDUCTION VIBRATION SENSOR AND REMOTE TEMPERATURE SENSOR FOR INDUSTRIAL INTELLIGENT MANUFACTURING	892
<i>Yu-Sheng Lai ; Shao-Hui Hsu ; Chun-Chi Chen ; Meiyi Li ; Ju-Mei Lu ; Hsu-Chun Cheng ; Jui-Min Liu ; Yen-Chang Chen ; Yu-Tsung Tuan ; Cheng-San Wu ; Jia-Min Shieh ; Wen-Kuan Yeh</i>	
40.5 - AN INTEGRATED PLASMONIC REFRACTIVE INDEX SENSOR: AL NANOHOLE ARRAYS ON GE PIN PHOTODIODES	896
<i>L. Augel ; S. Bechler ; R. Körner ; M. Oehme ; J. Schulze ; I. A. Fischer</i>	
40.6 - NANOFUIDICS FOR CELL AND DRUG DELIVERY	900
<i>N. Di Trani ; A. Grattoni ; M. Ferrari</i>	
Author Index	